NPN small signal transistor

multicomp

RoHS

Compliant



Collector Collector Base

Emitter

- **Pin Configuration:**
- 1. Base
- 2. Emitter
- 3. Collector

- Features:For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30Hz and 15kHz
- Complementary types: BCX71

Applications:

· General purpose transistor

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Value	Unit
Collector-base voltage	Vсво	45	V
Collector-emitter voltage	Vceo	45	V
Emitter-base voltage	Vebo	5	V
Collector current	lc	0.2	А
Collector power dissipation	Pc	0.2	W
		0.35	W*
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to 150	°C

* Mounted on a 7× 5 × 0.6mm Ceramic Substrate

Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Туре	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BVceo	45	-	-	V	Ic = 2mA
Emitter-base breakdown voltage	ВУево	5	-	-	V	Ic = 10μA
Collector-emitter cutoff current	ICES	-	-	0.1	μA	Vce = 45V
Emitter-base cutoff current	Іево	-	-	0.1	μA	VEB = 4V
Collector emitter acturation voltage	VCE(sat)1	-	-	0.55	V	Ic/IB = 10mA/ 0.25mA
Collector-emitter saturation voltage	VCE(sat)2	-	-	630	V	Ic/IB = 50mA/ 1.25mA





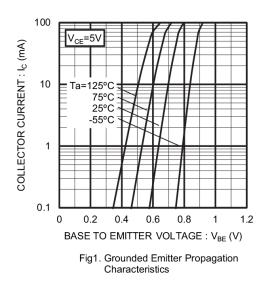
Electrical Characteristics (Ta = 25°C)

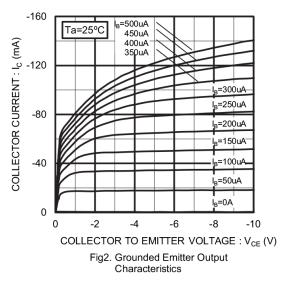
Parameter	Symbol	Min.	Туре	Max.	Unit	Conditions
	VBE(sat)1	-	-	-	V	Ic/IB = 10mA/ 0.25mA
Base-emitter saturation voltage	VBE(sat)2	-	-	-	V	Ic/IB = 50mA/ 1.25mA
Base-emitter voltage	VBE(on)	250	-	20	V	Vce = 5V, Ic = 2mA
DC current transfer ratio	hFE1	125 - 0.35		Vce = 5V, Ic = 2mA		
	hFE2	-	-	1.05	-	Vce = 5V, Ic = 50mA
Collector-base cutoff current	fτ	90	-	0.85	MHz	Vce = 5V, le = 10mA, f =100MHz
Transition frequency	Cob	0.55	-	0.75	μA	Vcb = 10V, f = 1MHz, IE = 0A
Collector output capacitance	NF	-	-	4.5	pF	Vce = 5V, lc = 200μA, f = 1kHz,Rg =2kΩ
Noise figure	Ісво	-	-	6	dB	Vсв = 45V, Ta = 150°С

This parts are classified into the categories below and given hFE item.

Part. No	BCX70J
hFE1	250 to 460
hFE2	90 or more

Electrical characteristics

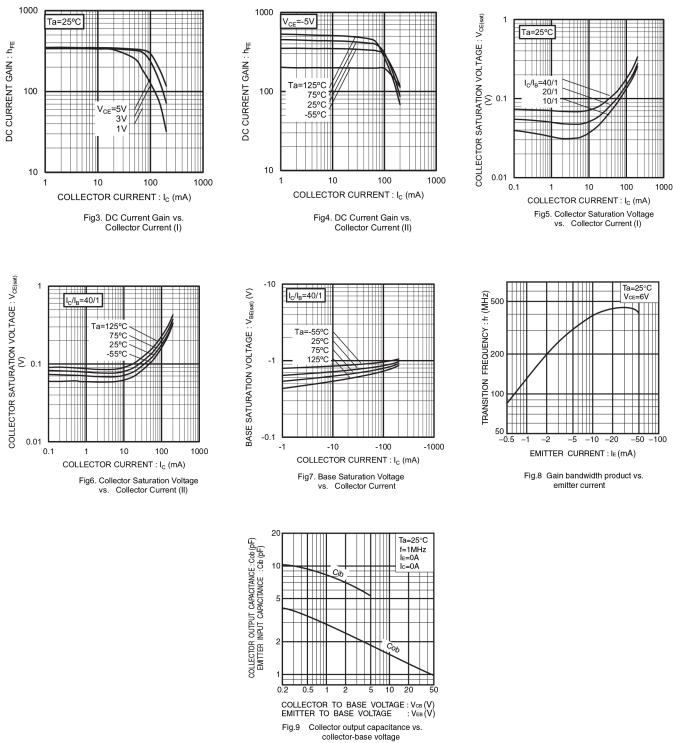






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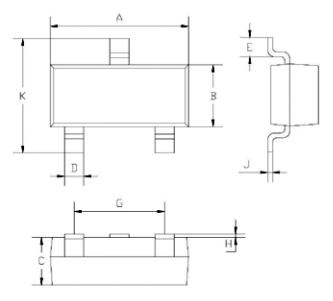
collector-base voltage Emitter input capacitance vs. emitter-base voltage





Package Outline

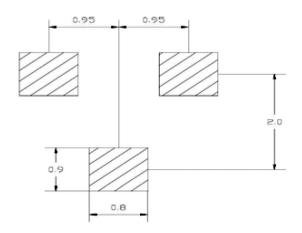
Plastic surface mounted package



Dimensions	Min.	Max.		
А	2.85	2.95		
В	1.25	1.35		
С	1 Typical			
D	0.4 Typical			
E	0.35	0.48		
G	1.85	1.95		
Н	0.02	0.1		
J	0.1 Typical			
К	2.35	2.45		

Dimensions : Millimetres

Soldering Footprint



Dimensions : Millimetres

Part Number Table

Description	Part Number	
Transistor, NPN, 0.1A, 45V, SOT-23	BCX70J	

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